

LF412 Low Offset, Low Drift Dual JFET Input Operational Amplifier

FEATURES

- Internally Trimmed Offset Voltage: 1 mV (max)
- Input Offset Voltage Drift: 10 μV/°C (max)
- Low Input Bias Current: 50 pA
- Low Input Noise Current: 0.01 pA / VHz
- Wide Gain Bandwidth: 3 MHz (min)
- High Slew Rate: 10V/µs (min)
- Low Supply Current: 1.8 mA/Amplifier
- High Input Impedance: 10¹²Ω
- Low Total Harmonic Distortion: ≤0.02%
- Low 1/f Noise Corner: 50 Hz
- Fast Settling Time to 0.01%: 2 µs

DESCRIPTION

These devices are low cost, high speed, JFET input operational amplifiers with very low input offset voltage and guaranteed input offset voltage drift. They require low supply current yet maintain a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The LF412 dual is pin compatible with the LM1558, allowing designers to immediately upgrade the overall performance of existing designs.

These amplifiers may be used in applications such as high speed integrators, fast D/A converters, sample and hold circuits and many other circuits requiring low input offset voltage and drift, low input bias current, high input impedance, high slew rate and wide bandwidth.

Typical Connection

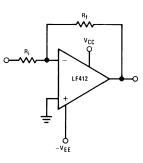


Figure 1.

Connection Diagram

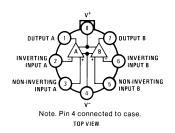


Figure 2. TO Package – Top View See Package Number NEV0008A

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Simplified Schematic



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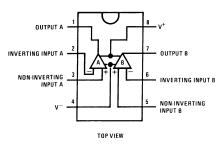
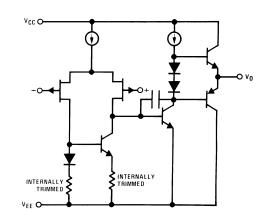


Figure 3. PDIP/CDIP Package – Top View See Package Number P0008E or NAB0008A



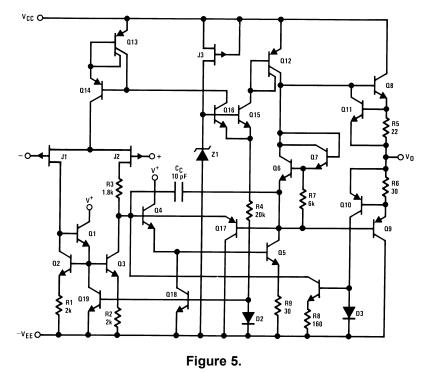
(1) Available per JM38510/11905

Figure 4. 1/2 Dual



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Detailed Schematic





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



Absolute Maximum Ratings (1) (2)

	LF412A	LF412	
Supply Voltage	±22V	±18V	
Differential Input Voltage	±38V	±30V	
Input voltage Range ⁽³⁾			
Output Short Circuit Duration (4)	Continuous	Continuous	
	TO Package	PDIP Package	
Power Dissipation ⁽⁵⁾	See ⁽⁶⁾	670 mW	
T _j max	150°C	115°C	
θ _{jA} (Typical)	152°C/W	115°C/W	
Operating Temp. Range	See ⁽⁷⁾	See (7)	
Storage Temp. Range	−65°C≤T _A ≤150°C	−65°C≤T _A ≤150°C	
Lead Temp. (Soldering, 10 sec.)	260°C	260°C	
ESD Tolerance ⁽⁸⁾	1700V	1700V	

"Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for (1) which the device is functional, but do not guarantee specific performance limits.

(2)Refer to RETS412X for LF412MH and LF412MJ military specifications.

Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage. (3)

Any of the amplifier outputs can be shorted to ground indefinitely, however, more than one should not be simultaneously shorted as the (4) maximum junction temperature will be exceeded.

Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the (5) part to operate outside guaranteed limits.

For operating at elevated temperature, these devices must be derated based on a thermal resistance of θ_{iA} . (6)

These devices are available in both the commercial temperature range 0°C<T_A<70°C and the military temperature range (7) -55°C≤T_A≤125°C. The temperature range is designated by the position just before the package type in the device number. A "C" indicates the commercial temperature range and an "M" indicates the military temperature range. The military temperature range is available in TO package only. In all cases the maximum operating temperature is limited by internal junction temperature Ti max.

(8) Human body model, 1.5 k Ω in series with 100 pF.

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DC Electrical Characteristics

Symbol	Parameter	Condi		LF412A ⁽¹)	LF412 ⁽¹⁾			Units	
			Min	Тур	Тур Мах		Min Typ			
V _{OS}	Input Offset Voltage	R _S =10 kΩ, T _A =25°C			0.5	1.0		1.0	3.0	mV
$\Delta V_{OS} / \Delta T$	Average TC of Input Offset Voltage	R_S =10 k Ω ⁽²⁾			7	10		7	20	µV/°C
I _{OS}	Input Offset Current	$V_{S}=\pm 15V^{(1)}$ (3)	T _j =25°C		25	100		25	100	pА
			T _j =70°C			2			2	nA
			T _j =125°C			25			25	nA
I _B	Input Bias Current	V _S =±15V ^{(1) (3)}	T _j =25°C		50	200		50	200	pА
			T _j =70°C			4			4	nA
			T _j =125°C			50			50	nA
R _{IN}	Input Resistance	T _i =25°C			10 ¹²			10 ¹²		Ω
A _{VOL}	Large Signal Voltage	R _L =2k, T _A =25°C	- 50	200		05	000			
	Gain	V _S =±15V, V _O =±10V				25	200		V/mV	
		Over Temperature	25	200		15	200		V/mV	
Vo	Output Voltage Swing	V _S =±15V, R _L =10k		±12	±13.5		±12	±13.5		V
V _{CM}	Input Common-Mode			±16	+19.5		±11	+14.5		V
	Voltage Range				-16.5			-11.5		V
CMRR	Common-Mode Rejection Ratio	R _S ≤10k		80	100		70	100		dB
PSRR	Supply Voltage Rejection Ratio			⁽⁴⁾ 80	100		70	100		dB
I _S	Supply Current	$V_0 = 0V, R_L = \infty$			3.6	5.6		3.6	6.5	mA

(1) Unless otherwise specified, the specifications apply over the full temperature range and for $V_S=\pm 20V$ for the LF412A and for $V_S=\pm 15V$ for the LF412. V_{OS} , I_B , and I_{OS} are measured at $V_{CM}=0$.

(2) The LF412A is 100% tested to this specification. The LF412 is sample tested on a per amplifier basis to insure at least 85% of the amplifiers meet this specification.

(3) The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T_j. Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, P_D. T_j=T_A+θ_{jA} P_D where θ_{jA} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

(4) Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously in accordance with common practice. V_S = ±6V to ±15V.

0	Demonstern	Conditions		LF412A ⁽¹)	LF412 ⁽¹⁾			1	
Symbol	Parameter	Conditions	Min	Тур	Max	Min	Тур	Max	Units	
	Amplifier to Amplifier Coupling	T _A =25°C, f=1 Hz-20 kHz (Input Referred)		-120			-120		dB	
SR	Slew Rate	V _S =±15V, T _A =25°C	10	15		8	15		V/µs	
GBW	Gain-Bandwidth Product	V _S =±15V, T _A =25°C	3	4		2.7	4		MHz	
THD	Total Harmonic Dist	A _V =+10, R _L =10k, V _O =20 Vp-p, BW=20 Hz-20 kHz		≤0.02			≤0.02		%	
e _n	Equivalent Input Noise Voltage	$T_A=25^{\circ}C, R_S=100\Omega, f=1 \text{ kHz}$		25			25		nV / √Hz	
i _n	Equivalent Input Noise Current	T _A =25°C, f=1 kHz		0.01			0.01		pA / √Hz	

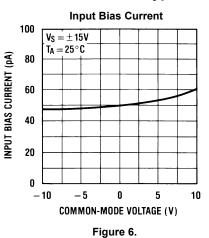
AC Electrical Characteristics

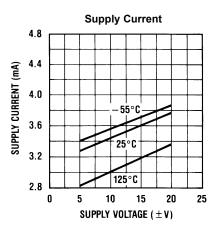
(1) Unless otherwise specified, the specifications apply over the full temperature range and for $V_S=\pm 20V$ for the LF412A and for $V_S=\pm 15V$ for the LF412. V_{OS} , I_B , and I_{OS} are measured at $V_{CM}=0$.

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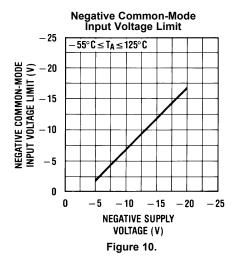
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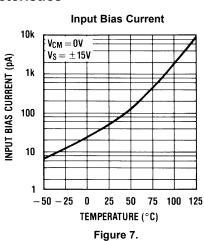




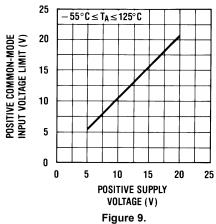


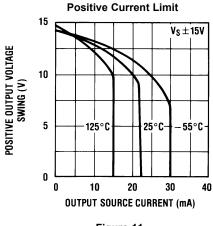






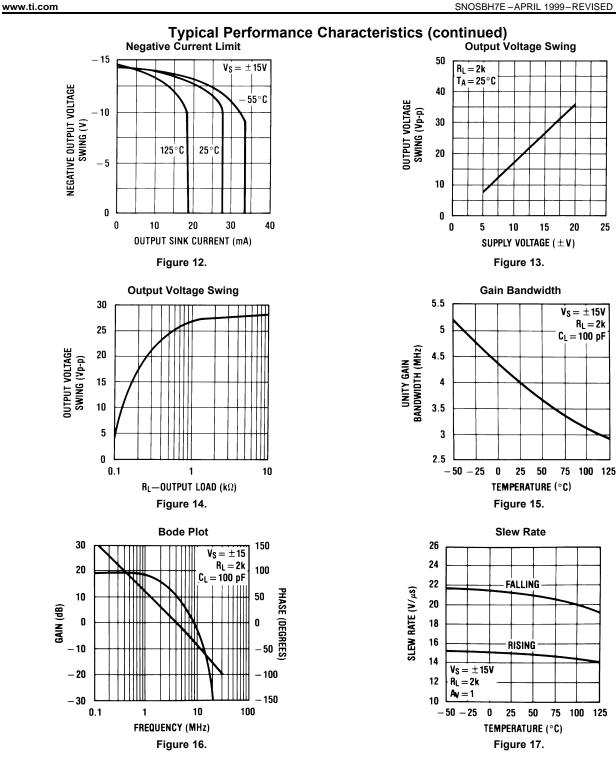
Positive Common-Mode Input Voltage Limit







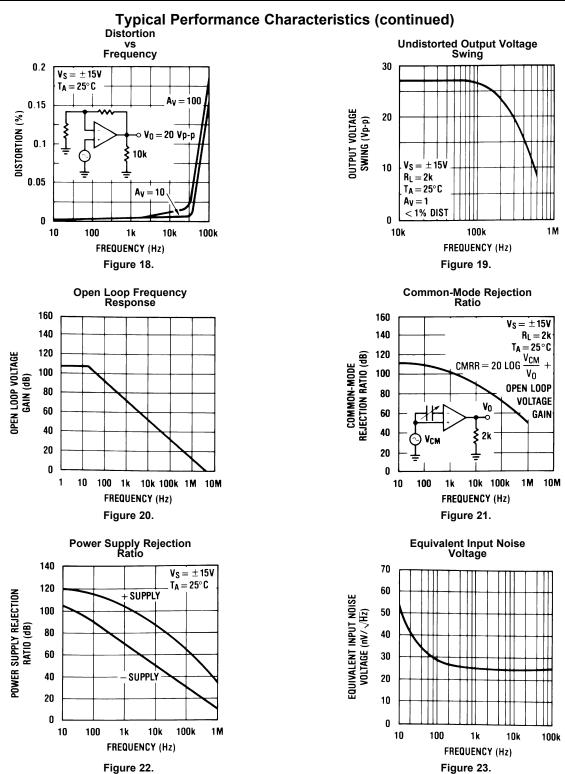
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TEXAS INSTRUMENTS

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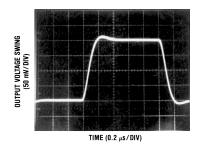


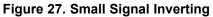
Typical Performance Characteristics (continued) Open Loop Voltage Gain Output **Output Impedance** 1M 100 $V_{S} = \pm 15V T_{A} = 25^{\circ}C$ $R_L = 2k$ $-55^{\circ}C \le T_{A} \le 125^{\circ}C$ open loop voltage gain (v/v) OUTPUT IMPEDANCE (Ω) Ш 10 $A_{V} = 100$ 100k 1 10k 0.1 5 10 15 20 100 10k 100k 1M 1k SUPPLY VOLTAGE (\pm V) FREQUENCY (Hz) Figure 25. Figure 24. **Inverter Settling Time** 10 10 mV ้1 ่ m V OUTPUT VOLTAGE SWING FROM OV (V) 5 0 - 5 10 mV 1 mV - 10 0.1 10 1 SETTLING TIME (µs)

Figure 26.

PULSE RESPONSE

 $R_L{=}2~k\Omega,~C_L{=}10~pF$





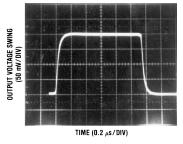
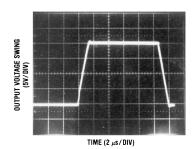


Figure 28. Small Signal Non-Inverting



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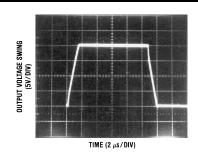


Figure 29. Large Signal Inverting



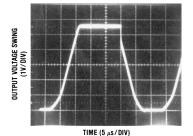


Figure 31. Current Limit (R_L=100Ω)

APPLICATION HINTS

The LF412 series of JFET input dual op amps are internally trimmed (BI-FET II[™]) providing very low input offset voltages and guaranteed input offset voltage drift. These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore, large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will cause a reversal of the phase to the output and force the amplifier output to the corresponding high or low state.

Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output, however, if both inputs exceed the limit, the output of the amplifier may be forced to a high state.

The amplifiers will operate with a common-mode input voltage equal to the positive supply; however, the gain bandwidth and slew rate may be decreased in this condition. When the negative common-mode voltage swings to within 3V of the negative supply, an increase in input offset voltage may occur.

Each amplifier is individually biased by a zener reference which allows normal circuit operation on $\pm 6.0V$ power supplies. Supply voltages less than these may result in lower gain bandwidth and slew rate.

The amplifiers will drive a 2 k Ω load resistance to ±10V over the full temperature range. If the amplifier is forced to drive heavier load currents, however, an increase in input offset voltage may occur on the negative voltage swing and finally reach an active current limit on both positive and negative swings.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

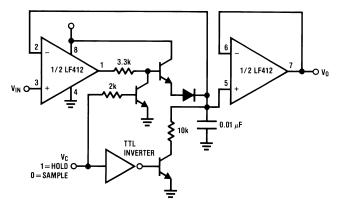
As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.



A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately 6 times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

TYPICAL APPLICATION





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REVISION HISTORY

Cł	nanges from Revision D (March 2013) to Revision E	Page
•	Changed layout of National Data Sheet to TI format	11

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing		Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings
LF412ACN	ACTIVE	PDIP	Р	8	40	TBD	Call TI	Call TI	0 to 70	LF 412ACN
LF412ACN/NOPB	ACTIVE	PDIP	Р	8	40	Green (RoHS & no Sb/Br)	Call TI	Level-1-NA-UNLIM	0 to 70	LF 412ACN
LF412CN	ACTIVE	PDIP	Р	8	40	TBD	Call TI	Call TI	0 to 70	LF 412CN
LF412CN/NOPB	ACTIVE	PDIP	Р	8	40	Green (RoHS & no Sb/Br)	Call TI	Level-1-NA-UNLIM	0 to 70	LF 412CN
LF412MH	ACTIVE	то	NEV	8	500	TBD	Call TI	Call TI	-55 to 125	LF412MH
LF412MH/NOPB	ACTIVE	то	NEV	8	500	Green (RoHS & no Sb/Br)	POST-PLATE	Level-1-NA-UNLIM	-55 to 125	LF412MH

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

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Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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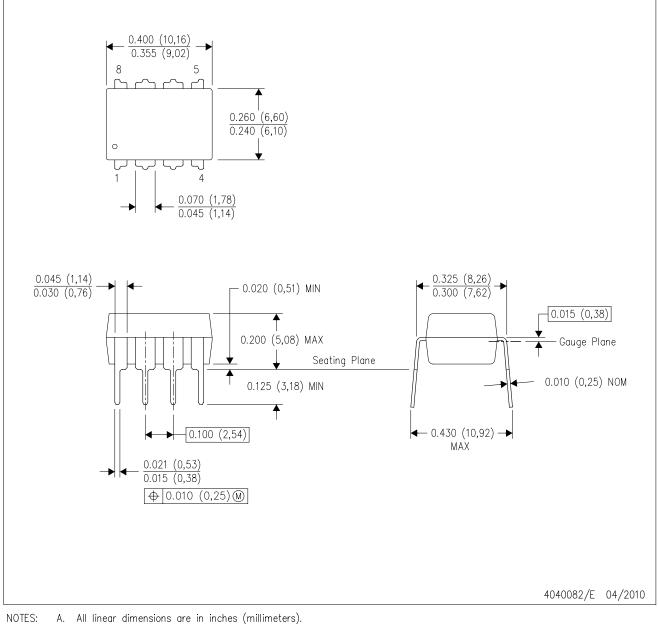
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PLASTIC DUAL-IN-LINE PACKAGE

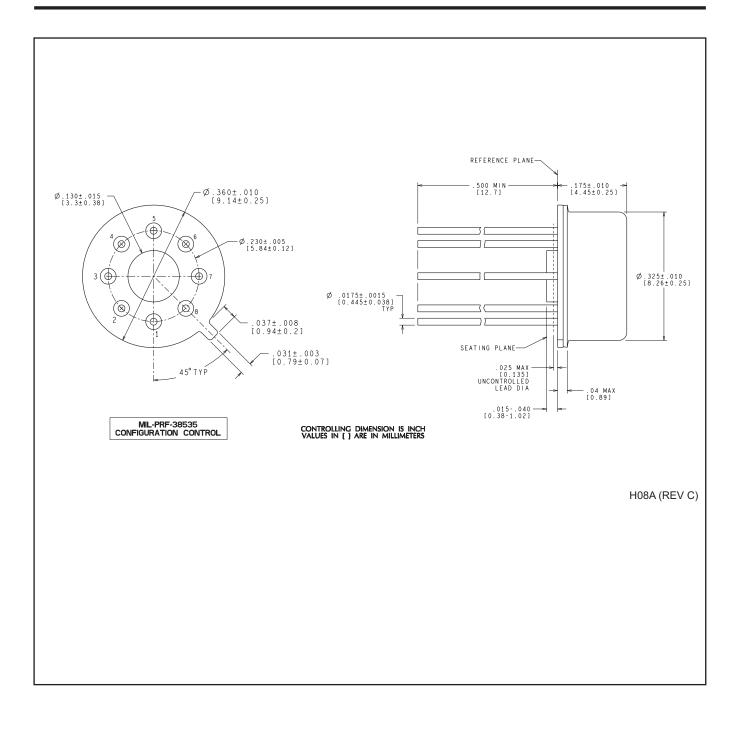


- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



MECHANICAL DATA

NEV0008A



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